Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- · AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | - | -5 | Α |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -5 \text{ A}; T_j = 25 \text{ °C}$ | | - | 39 | 48 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol | |
|-----|--------|-------------|-----------------------------|---|--|
| 1 | D | drain | 15/ | D | |
| 2 | D | drain | 7 7 | | |
| 3 | G | gate | 2 5 | G \downarrow \downarrow \downarrow \downarrow | |
| 4 | S | source | 3 8 4 Transparent top view | Transparent top view | |
| 5 | D | drain | | | |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | \$ | |
| 7 | D | drain | | 017aaa259 | |
| 8 | S | source | | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|-------------|---|---------|--|--|--|
| | Name | Description | Version | | | |
| PMPB43XPEA | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB43XPEA | 4M |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|---|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -5 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -3.1 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | -12 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 1.7 | W |
| | | T _{sp} = 25 °C | | - | 12.5 | W |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drai | n diode | | | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | -1.9 | Α |
| ESD maxim | um rating | | | | | |
| V_{ESD} | electrostatic discharge voltage | НВМ | [2] | - | 1000 | V |
| Avalanche r | uggedness | | ' | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $T_{j(init)}$ = 25 °C; I_D = -1.2 A; DUT in avalanche (unclamped) | | - | 12.6 | mJ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Measured between all pins.

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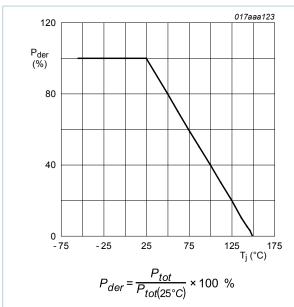


Fig. 1. Normalized total power dissipation as a function of junction temperature

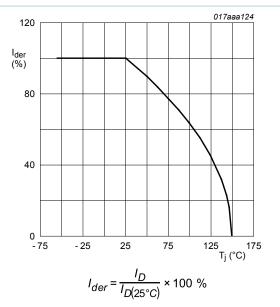
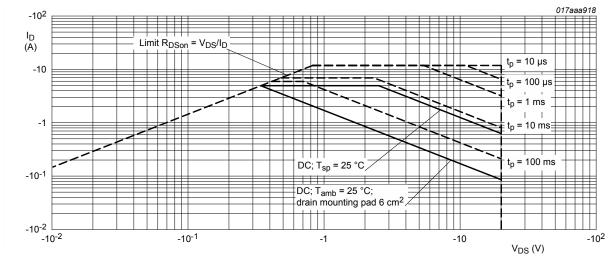


Fig. 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | | [1] | - | 235 | 270 | K/W |
| | | | [2] | - | 67 | 74 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 5 | 10 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

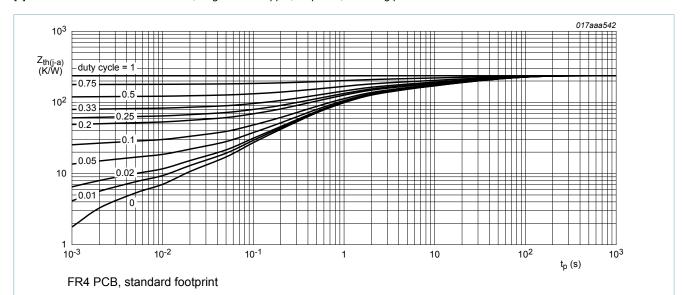


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

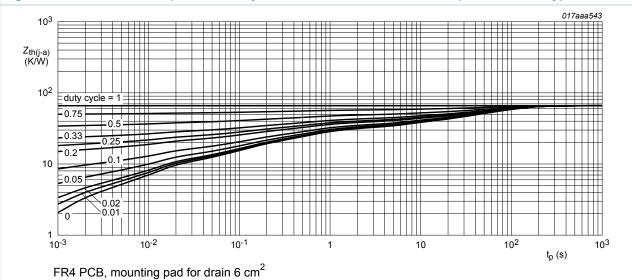


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|--|------|------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | -0.4 | -0.7 | -1 | V |
| I _{DSS} | drain leakage current | V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C | - | - | -1 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | -10 | μΑ |
| | | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μΑ |
| R_{DSon} | drain-source on-state | V _{GS} = -4.5 V; I _D = -5 A; T _j = 25 °C | - | 39 | 48 | mΩ |
| | resistance | V _{GS} = -4.5 V; I _D = -5 A; T _j = 150 °C | - | 55 | 68 | mΩ |
| | | V_{GS} = -2.5 V; I_D = -4.5 A; T_j = 25 °C | - | 45 | 59 | mΩ |
| | | V_{GS} = -1.8 V; I_D = -3.7 A; T_j = 25 °C | - | 56 | 79 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = -10 V; I_D = -5 A; T_j = 25 °C | - | 20 | - | S |
| R_G | gate resistance | f = 1 MHz | - | 5.6 | - | Ω |
| Dynamic ch | naracteristics | | ' | | | , |
| Q _{G(tot)} | total gate charge | V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; | - | 15.6 | 23.4 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 1.9 | - | nC |
| Q_{GD} | gate-drain charge | | - | 3.4 | - | nC |
| C _{iss} | input capacitance | V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V; | - | 1550 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 142 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 116 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; | - | 9 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 38 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 57 | - | ns |
| t _f | fall time | | - | 25 | - | ns |
| Source-dra | in diode | | 1 | , | | |
| V_{SD} | source-drain voltage | I_S = -1.9 A; V_{GS} = 0 V; T_j = 25 °C | - | -0.7 | -1.2 | V |
| t _{rr} | reverse recovery time | $I_S = -1.9 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$ | - | 19 | - | ns |
| | | $V_{GS} = 0 \text{ V}; V_{DS} = -10 \text{ V}; T_i = 25 \text{ °C}$ | | _ | | |

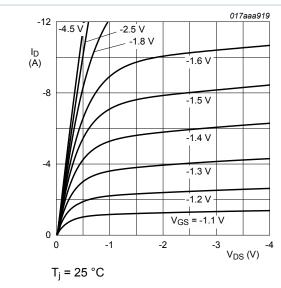


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

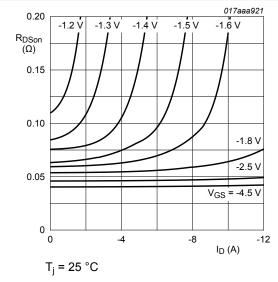


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

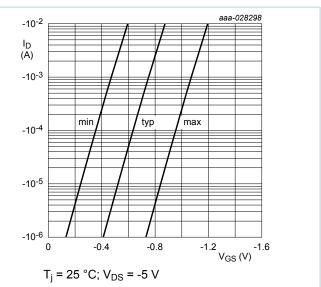


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

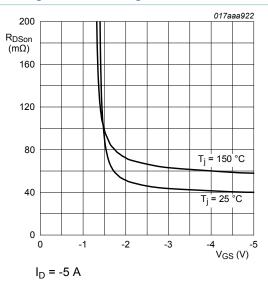


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

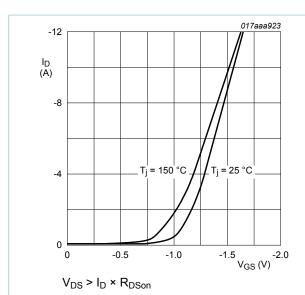


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

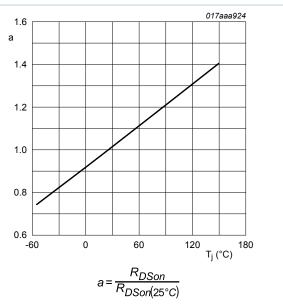


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

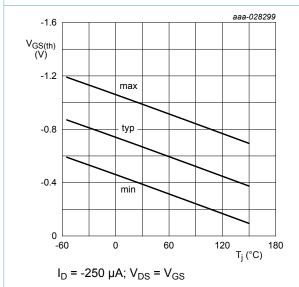


Fig. 12. Gate-source threshold voltage as a function of junction temperature

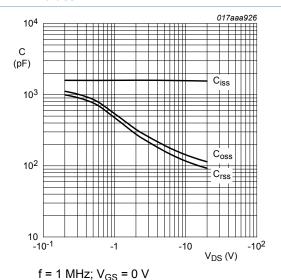


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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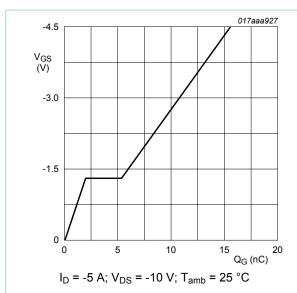


Fig. 14. Gate-source voltage as a function of gate charge; typical values

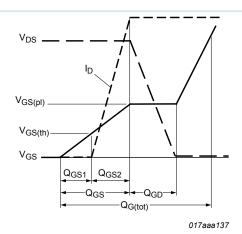


Fig. 15. MOSFET transistor: Gate charge waveform definitions

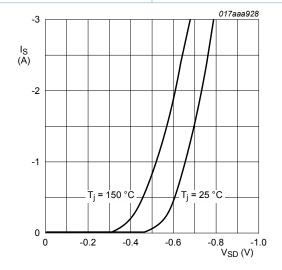
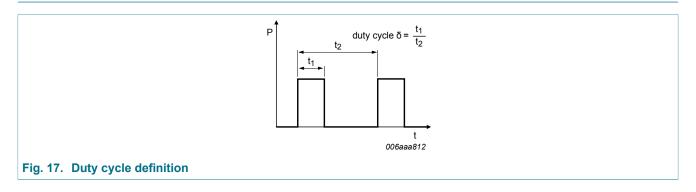


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

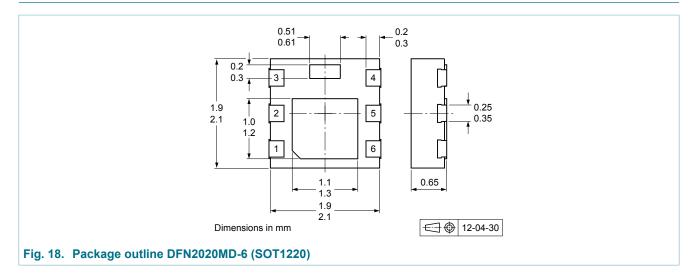
11. Test information



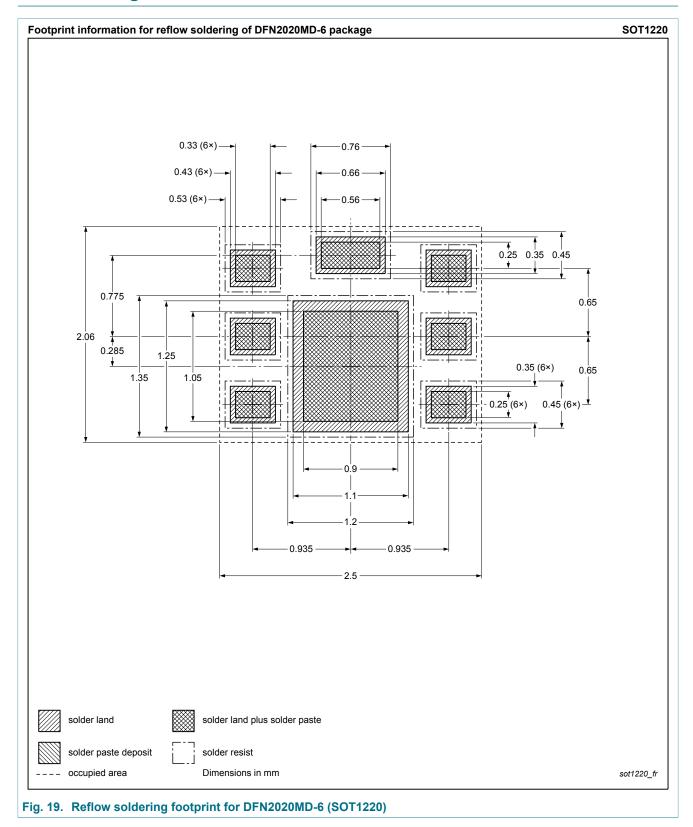
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMPB43XPEA v.1 | 20180327 | Product data sheet | - | - |

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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